

## Excellent Integrated System Limited

Stocking Distributor

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[International Rectifier \(Infineon Technologies Americas Corp.\)  
IRLR7811WPBF](#)

For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)

International  
**IR** Rectifier

**SMPS MOSFET**

PD - 95778A

**IRLR7811WPbF**

**Applications**

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- Lead-Free

HEXFET® Power MOSFET

V <sub>DSS</sub>	R <sub>DS(on)</sub> max	Q <sub>g</sub>
30V	10.5mΩ	19nC

**Benefits**

- Very Low RDS(on) at 4.5V V<sub>GS</sub>
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	64 <sup>④</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	45 <sup>④</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	260	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	71	
P <sub>D</sub> @ T <sub>A</sub> = 100°C	Power Dissipation*	1.5	W
	Linear Derating Factor	0.48	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	V
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	2.1	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB mount)*	—	50	
R <sub>θJA</sub>	Junction-to-Ambient	—	110	

Notes <sup>①</sup> through <sup>④</sup> are on page 9  
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**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions	
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	27	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA ⑥	
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	5.8	10.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A ④	
		—	7.0	15		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A	
V <sub>GS(th)</sub>	Gate Threshold Voltage	—	1.5	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-5.0	—	mV/°C		
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	30	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	
		—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C	
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 12V	
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -12V	
g <sub>fs</sub>	Forward Transconductance	58	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 12A	
Q <sub>g</sub>	Total Gate Charge Control Fet	—	21	31	nC		
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-Source Charge	—	5.0	—			
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-Source Charge	—	1.7	—			
Q <sub>gd</sub>	Gate-to-Drain Charge	—	6.6	—			
Q <sub>godr</sub>	Gate Charge Overdrive	—	5.5	—			
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	8.3	—			
Q <sub>g</sub>	Total Gate Charge Sync Fet	—	17	—			
Q <sub>oss</sub>	Output Charge	—	10	—			V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>g</sub>	Gate Resistance	—	1.6	—			
t <sub>d(on)</sub>	Turn-On Delay Time	—	18	—			ns
t <sub>r</sub>	Rise Time	—	4.8	—			
t <sub>d(off)</sub>	Turn-Off Delay Time	—	11	—			
t <sub>f</sub>	Fall Time	—	23	—			
C <sub>iss</sub>	Input Capacitance	—	2260	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 15V f = 1.0MHz	
C <sub>oss</sub>	Output Capacitance	—	420	—			
C <sub>rss</sub>	Reverse Transfer Capacitance	—	180	—			

**Avalanche Characteristics**

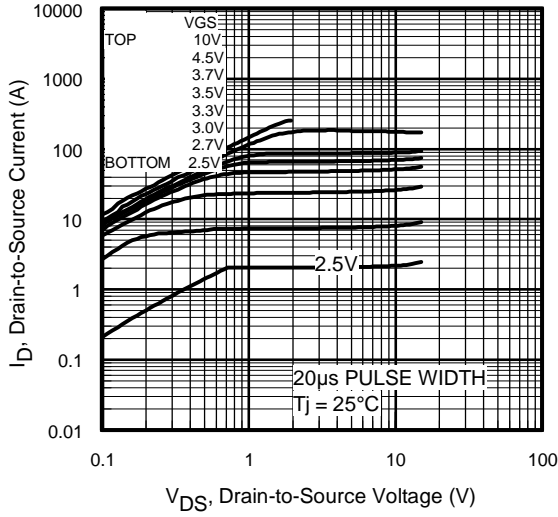
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	140	mJ
I <sub>AR</sub>	Avalanche Current③	—	12	A
E <sub>AR</sub>	Repetitive Avalanche Energy③	—	7.1	mJ

**Diode Characteristics**

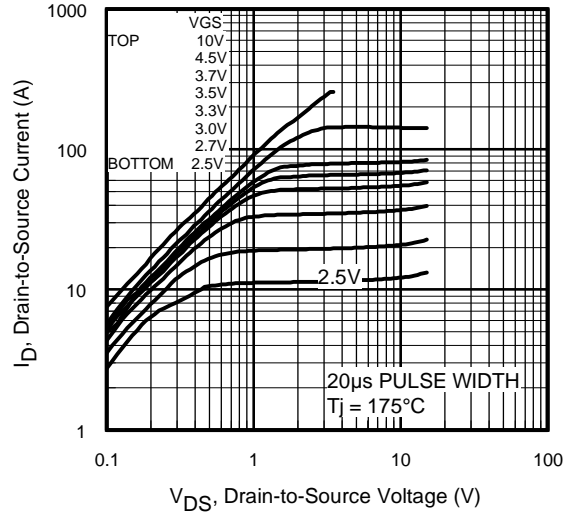
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	64④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	260		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 12A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	30	45	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 12A
Q <sub>rr</sub>	Reverse Recovery Charge	—	27	41	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

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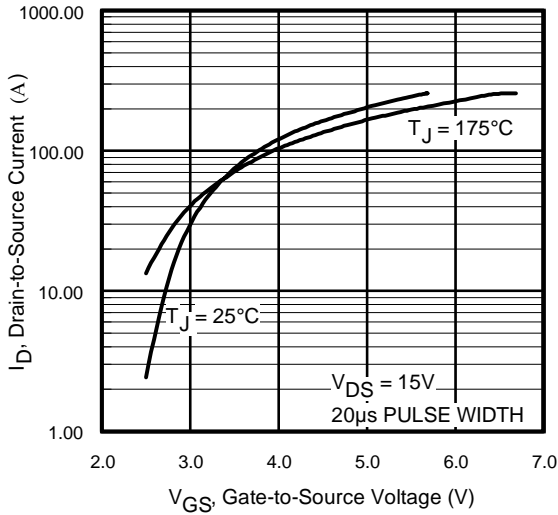
# IRLR7811WPbF



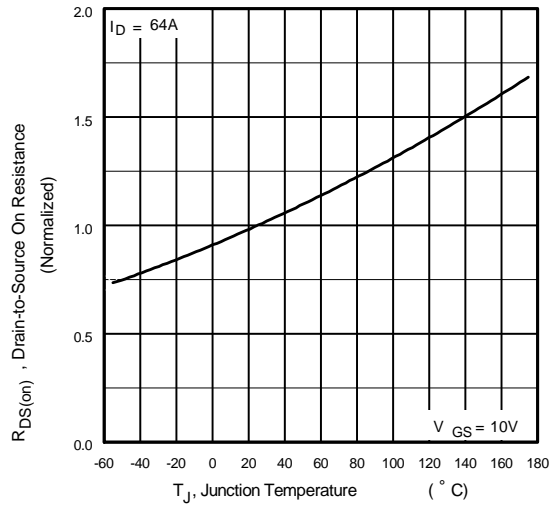
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



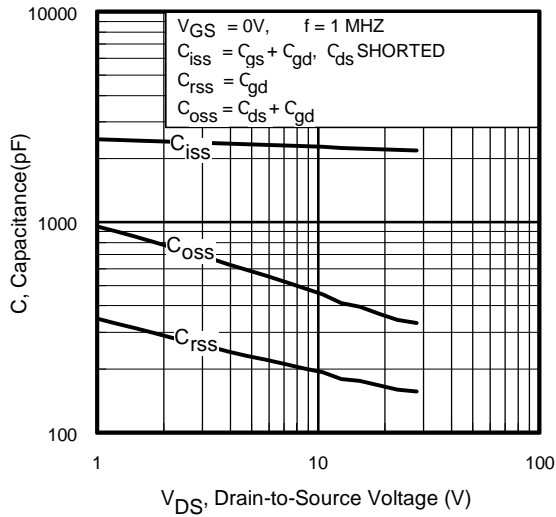
**Fig 3.** Typical Transfer Characteristics



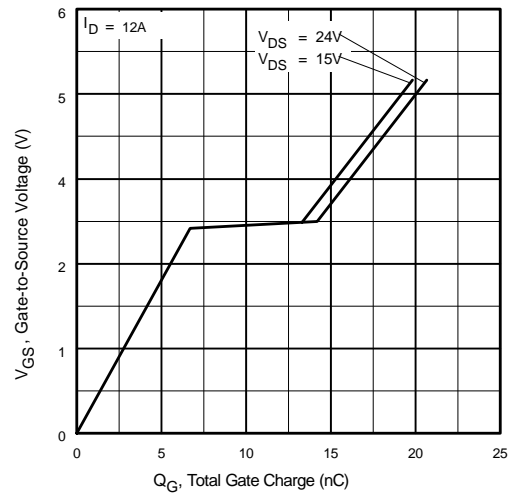
**Fig 4.** Normalized On-Resistance Vs. Temperature

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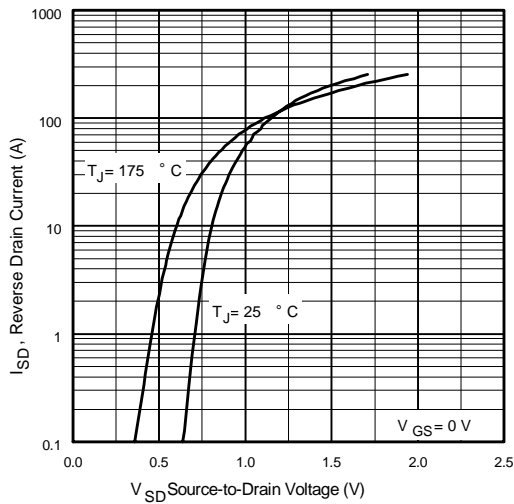
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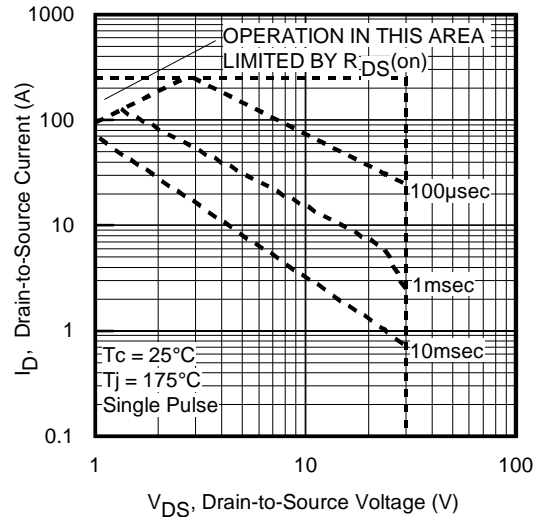
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



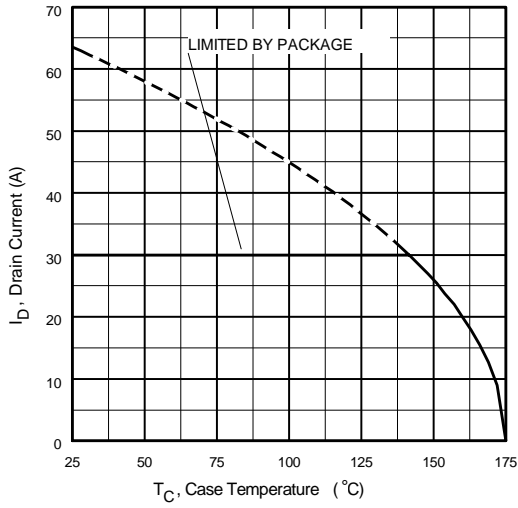
**Fig 7.** Typical Source-Drain Diode Forward Voltage



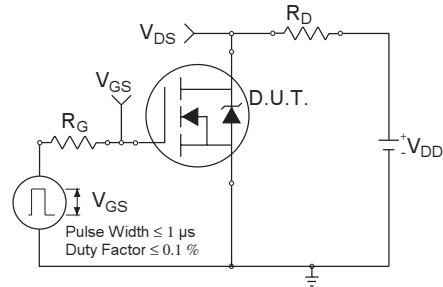
**Fig 8.** Maximum Safe Operating Area

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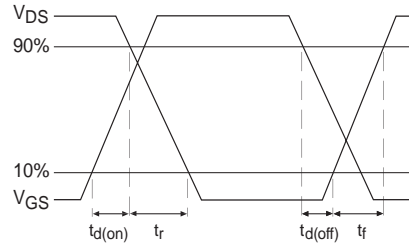
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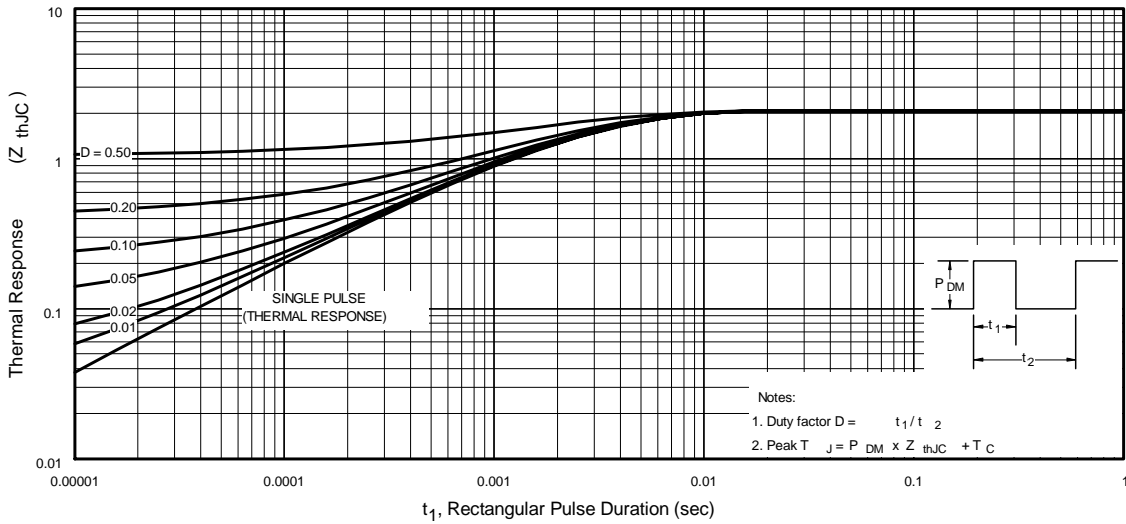
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



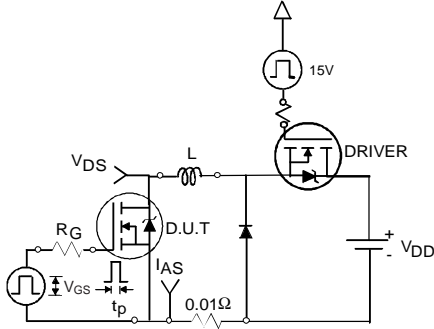
**Fig 10b.** Switching Time Waveforms



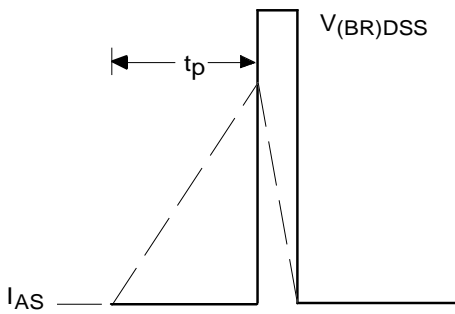
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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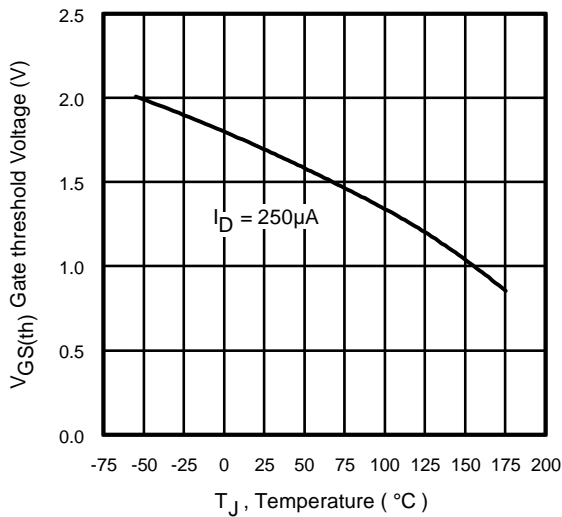
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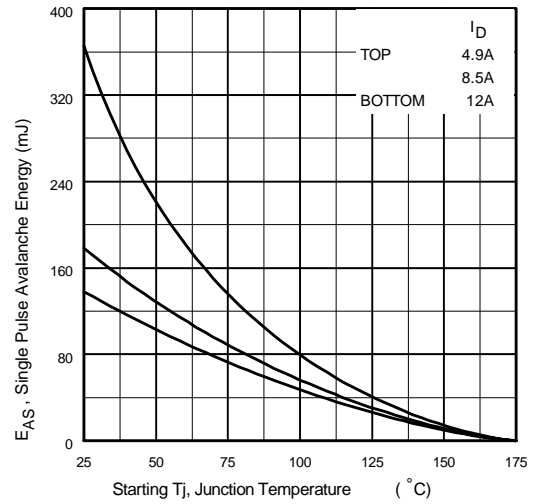
**Fig 12a.** Unclamped Inductive Test Circuit



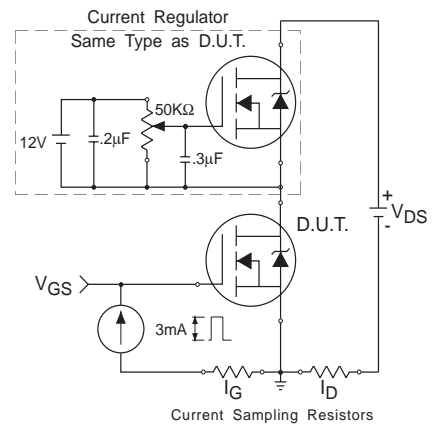
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13.** Threshold Voltage Vs. Temperature

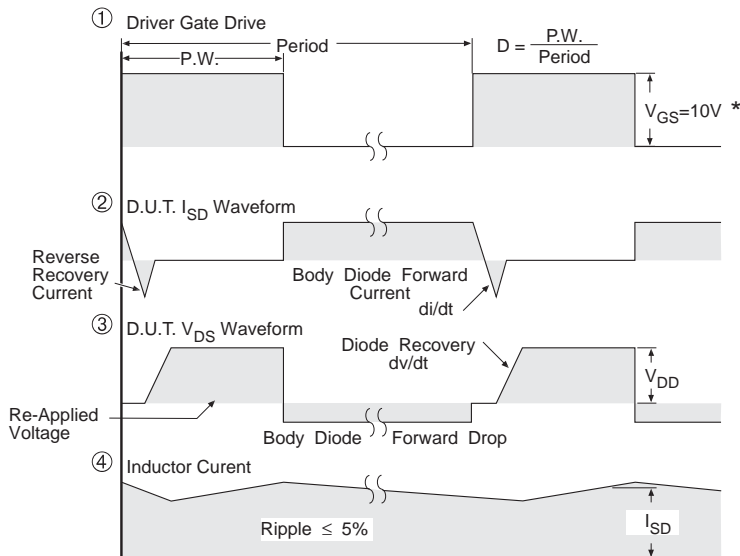
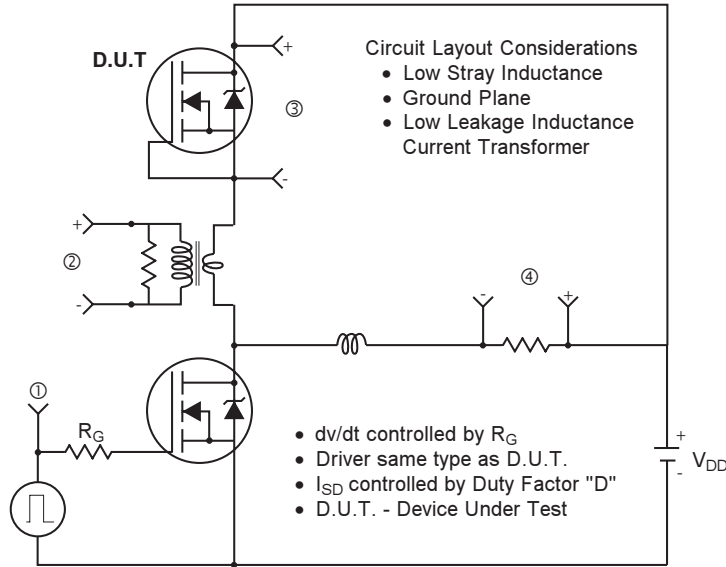


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 15.** For N-Channel HEXFET® Power MOSFETs

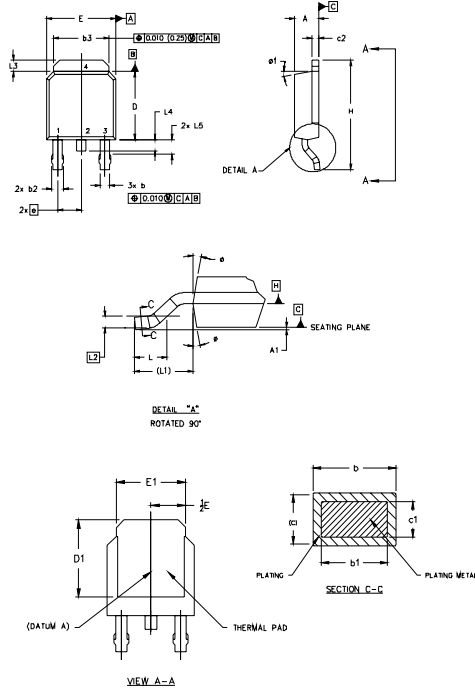


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## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS).
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

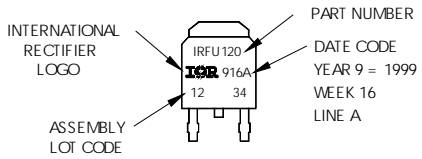
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	.0051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
phi	0"	.10"	0"	.10"	
phi1	0"	.15"	0"	.15"	

- LEAD ASSIGNMENTS**
- HEXFET**
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN
- IGBTs, CoPACK**
- 1.- GATE
  - 2.- COLLECTOR
  - 3.- EMITTER
  - 4.- COLLECTOR

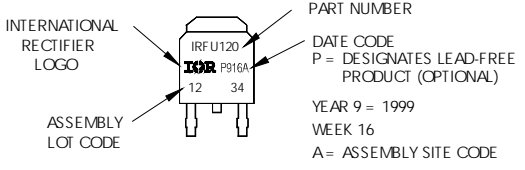
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
 WITH ASSEMBLY  
 LOT CODE 1234  
 ASSEMBLED ON WW16, 1999  
 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
 indicates "Lead-Free"



OR

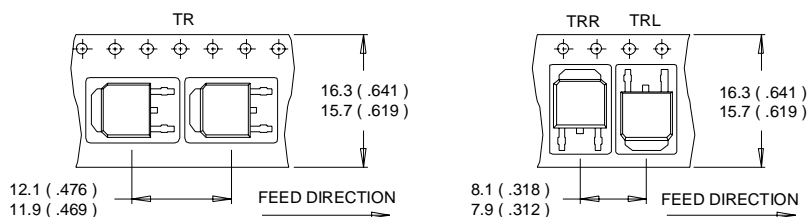


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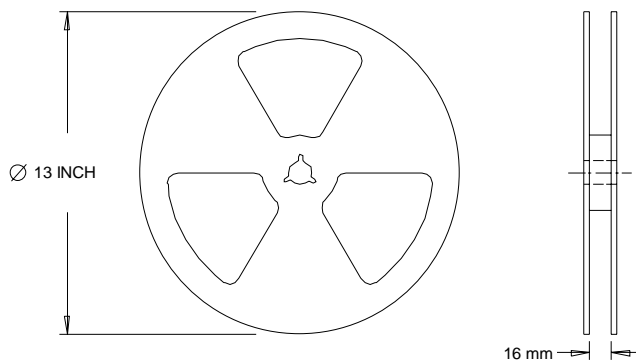
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
  - ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 1.9\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 12\text{A}$ .
  - ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
  - ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- \* When mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.

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TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.01/05

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>